

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-31 (Canceled).

32. (Currently Amended) A light emitting device comprising:

a plurality of gate signal lines over a substrate;

a plurality of source signal lines crossing the plurality of gate signal lines;

a plurality of first power supply lines along the plurality of gate signal lines; and

a plurality of second power supply lines along the plurality of source signal lines,

wherein the plurality of first power supply lines are made from a same material as the plurality of gate signal lines; and

wherein one of the plurality of first power supply lines and one of the plurality of second power supply lines are connected through ~~contact holes~~ a contact hole.

33. (Currently Amended) A light emitting device comprising:

a plurality of thin film transistors over a substrate comprising impurity regions and a channel region disposed between the impurity regions;

a plurality of gate signal lines over the plurality of thin film transistors;

a plurality of source signal lines crossing the plurality of gate signal lines;

a plurality of first power supply lines along the plurality of gate signal lines; and

a plurality of second power supply lines along the plurality of source signal lines,

wherein the plurality of first power supply lines are made from a same material as the plurality of gate signal lines;

wherein one of the plurality of first power supply lines and one of the plurality of second power supply lines are connected through ~~contact holes~~ a contact hole; and

wherein one of impurity regions is connected with one of the plurality of second power supply lines.

34. (Previously Presented) A light emitting device comprising:

a base film over a substrate;

a semiconductor layer having impurity regions and a channel region disposed between the impurity regions over the base film;

a gate insulating film over the semiconductor layer;

a gate electrode over the gate insulating film;

a source signal line over the semiconductor layer;

a power supply line over the source signal line; and

a light emitting element over the power supply line, comprising a first electrode, a second electrode and an electroluminescence layer disposed between the first and second electrodes,

wherein one of the impurity regions is electrically connected with the power supply line and another one of the impurity regions is electrically connected with the first electrode; and

wherein the gate electrode comprises a same material as the power supply line.

35. (Previously Presented) A light emitting device comprising:

a base film over a substrate;

a semiconductor layer having impurity regions and a channel region disposed between the impurity regions over the base film;

a gate insulating film over the semiconductor layer;

a gate electrode over the gate insulating film;

a source signal line over the semiconductor layer;

a passivation film over the source signal line;

a power supply line over the source signal line, and through a contact hole formed in the passivation film; and

a light emitting element over the power supply line, comprising a first electrode, a second electrode and an electroluminescence layer disposed between the first and second electrodes,

wherein one of the impurity regions is electrically connected with the power supply line and another one of the impurity regions is electrically connected with the first electrode; and

wherein the gate electrode comprises a same material as the power supply line.

36. (Previously Presented) A light emitting device comprising:

a base film over a substrate;

a semiconductor layer having impurity regions and a channel region disposed between the impurity regions over the base film;

a gate insulating film over the semiconductor layer;

a gate electrode over the gate insulating film;

a source signal line over the semiconductor layer;

a power supply line over the source signal line; and

a light emitting element over the power supply line, comprising a first electrode comprising ITO, a second electrode and an electroluminescence layer disposed between the first and second electrodes,

wherein one of the impurity regions is electrically connected with the power supply line and another one of the impurity regions is electrically connected with the first electrode, and

wherein the gate electrode comprises a same material as the power supply line.

37. (Previously Presented) A light emitting device comprising:

a power supply line over a substrate;

a base film over the power supply line;

a semiconductor layer having impurity regions and a channel region disposed between the impurity regions over the base film;

a gate insulating film over the semiconductor layer;

a gate electrode over the gate insulating film; and

a light emitting element over the gate electrode, comprising a first electrode, a second electrode and an electroluminescence layer disposed between the first and second electrodes,

wherein one of the impurity regions is electrically connected with the power supply line and another one of the impurity regions is electrically connected with the first electrode.

38. (Previously Presented) A light emitting device comprising:

a power supply line over a substrate;

a base film over the power supply line;

a semiconductor layer having impurity regions and a channel region disposed between the impurity regions over the base film;

a gate insulating film over the semiconductor layer;

a gate electrode over the gate insulating film;

a passivation film over the gate electrode; and

a light emitting element over the gate electrode, comprising a first electrode, a second electrode and an electroluminescence layer disposed between the first and second electrodes,

wherein one of the impurity regions is electrically connected with the power supply line and another one of the impurity regions is electrically connected with the first electrode.

39. (Previously Presented) A light emitting device comprising:

a power supply line over a substrate;

a base film over the power supply line;

a semiconductor layer having impurity regions and a channel region disposed between the impurity regions over the base film;

a gate insulating film over the semiconductor layer;

a gate electrode over the gate insulating film; and

a light emitting element over the gate electrode, comprising a first electrode comprising ITO, a second electrode and an electroluminescence layer disposed between the first and second electrodes,

wherein one of the impurity regions is electrically connected with the power supply line and another one of the impurity regions is electrically connected with the first electrode.

40. (Currently Amended) A light emitting device according to claim ~~36~~ 35, wherein the passivation film comprises silicon nitride oxide or silicon nitride.

41. (Currently Amended) A light emitting device according to claim ~~39~~ 38, wherein the passivation film comprises silicon nitride oxide or silicon nitride.

42. (Previously Presented) A light emitting device according to claims 32, wherein the light emitting device is used in an electronic equipment selected from the group consisting of a personal computer, a video camera, a head mounted display, an image playback device, a mobile computer and a TV receiver.

43. (Previously Presented) A light emitting device according to claims 33, wherein the light emitting device is used in an electronic equipment selected from the group consisting of a personal computer, a video camera, a head mounted display, an image playback device, a mobile computer and a TV receiver.

44. (Previously Presented) A light emitting device according to claims 34, wherein the light emitting device is used in an electronic equipment selected from the group consisting of a personal computer, a video camera, a head mounted display, an image playback device, a mobile computer and a TV receiver.

45. (Previously Presented) A light emitting device according to claims 35, wherein the light emitting device is used in an electronic equipment selected from the group consisting of a

personal computer, a video camera, a head mounted display, an image playback device, a mobile computer and a TV receiver.

46. (Previously Presented) A light emitting device according to claims 36, wherein the light emitting device is used in an electronic equipment selected from the group consisting of a personal computer, a video camera, a head mounted display, an image playback device, a mobile computer and a TV receiver.

47. (Previously Presented) A light emitting device according to claims 37, wherein the light emitting device is used in an electronic equipment selected from the group consisting of a personal computer, a video camera, a head mounted display, an image playback device, a mobile computer and a TV receiver.

48. (Previously Presented) A light emitting device according to claims 38, wherein the light emitting device is used in an electronic equipment selected from the group consisting of a personal computer, a video camera, a head mounted display, an image playback device, a mobile computer and a TV receiver.

49. (Previously Presented) A light emitting device according to claims 39, wherein the light emitting device is used in an electronic equipment selected from the group consisting of a personal computer, a video camera, a head mount display, an image playback device, a mobile computer and a TV receiver.